PowerMOS transistor BUK437-400B

GENERAL DESCRIPTION

N-channel enhancement mode field-effect power transistor in a plastic envelope.
The device is intended for use in Switched Mode Power Supplies (SMPS), motor control, welding, DC/DC and AC/DC converters, and in general purpose switching applications.

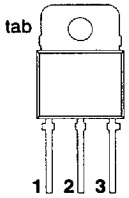
QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT
V_{DS}	Drain-source voltage	400	V
I_D	Drain current (DC)	12	A
P_{tot}	Total power dissipation	180	W
$R_{DS(ON)}$	Drain-source on-state resistance	0.5	Ω

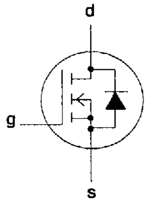
PINNING - SOT93

PIN	DESCRIPTION
1	gate
2	drain
3	source
tab	drain

PIN CONFIGURATION



SYMBOL



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{DS}	Drain-source voltage	-	-	400	V
V_{DGR}	Drain-gate voltage	$R_{GS} = 20\ k\Omega$	-	400	V
$\pm V_{GS}$	Gate-source voltage	-	-	30	V
I_D	Drain current (DC)	$T_{mb} = 25\ ^{\circ}C$	-	12	A
I_D	Drain current (DC)	$T_{mb} = 100\ ^{\circ}C$	-	7.6	A
I_{DM}	Drain current (pulse peak value)	$T_{mb} = 25\ ^{\circ}C$	-	48	A
P_{tot}	Total power dissipation	$T_{mb} = 25\ ^{\circ}C$	-	180	W
T_{stg}	Storage temperature	-	- 55	150	°C
T_j	Junction Temperature	-	-	150	°C

THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$R_{th\ j\text{-}mb}$	Thermal resistance junction to mounting base		-	-	0.69	K/W
$R_{th\ j\text{-}a}$	Thermal resistance junction to ambient		-	45	-	K/W

STATIC CHARACTERISTICS

T_{mb} = 25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$V_{(BR)DSS}$	Drain-source breakdown voltage	V_{GS} = 0 V; I_D = 0.25 mA	400	-	-	V
$V_{GS(TO)}$	Gate threshold voltage	V_{DS} = V_{GS}; I_D = 1 mA	2.1	3.0	4.0	V
I_{DSS}	Zero gate voltage drain current	V_{DS} = 400 V; V_{GS} = 0 V; T_j = 25 °C	-	2	20	µA
I_{DSS}	Zero gate voltage drain current	V_{DS} = 400 V; V_{GS} = 0 V; T_j =125 °C	-	0.1	1.0	mA
I_{GSS}	Gate source leakage current	V_{GS} = ±30 V; V_{DS} = 0 V	-	10	100	nA
$R_{DS(ON)}$	Drain-source on-state resistance	V_{GS} = 10 V; I_D = 6.5 A	-	0.45	0.5	Ω

DYNAMIC CHARACTERISTICS

T_{mb} = 25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
g_{fs}	Forward transconductance	V_{DS} = 25 V; I_D = 6.5 A	5.0	8.0	-	S
C_{iss}	Input capacitance	V_{GS} = 0 V; V_{DS} = 25 V; f = 1 MHz	-	1500	1800	pF
C_{oss}	Output capacitance		-	170	270	pF
C_{rss}	Feedback capacitance		-	70	120	pF
$t_{d\,on}$	Turn-on delay time	V_{DD} = 30 V; I_D = 2.8 A; V_{GS} = 10 V; R_{GS} = 50 Ω; R_{gen} = 50 Ω	-	20	40	ns
t_r	Turn-on rise time		-	60	90	ns
$t_{d\,off}$	Turn-off delay time		-	200	250	ns
t_f	Turn-off fall time		-	75	90	ns
L_d	Internal drain inductance	Measured from contact screw on tab to centre of die	-	5	-	nH
L_d	Internal drain inductance	Measured from drain lead 6 mm from package to centre of die	-	5	-	nH
L_s	Internal source inductance	Measured from source lead 6 mm from package to source bond pad	-	12.5	-	nH

REVERSE DIODE LIMITING VALUES AND CHARACTERISTICS

T_{mb} = 25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{DR}	Continuous reverse drain current	-	-	-	14	A
I_{DRM}	Pulsed reverse drain current	-	-	-	56	A
V_{SD}	Diode forward voltage	I_F = 14 A ;V_{GS} = 0 V	-	1.1	1.4	V
t_{rr}	Reverse recovery time	I_F = 14 A; -dI_F/dt = 100 A/µs; V_{GS} = 0 V; V_R = 100 V	-	500	-	ns
Q_{rr}	Reverse recovery charge		-	6.0	-	µC

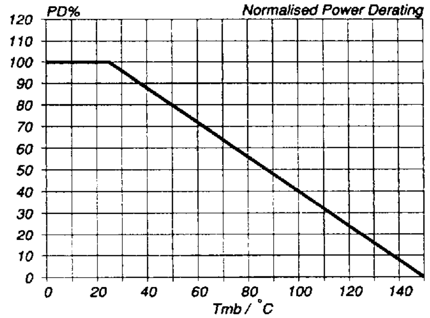


Fig.1. Normalised power dissipation. PD% = $100 \cdot P_D/P_{D\,25\,^\circ C} = f(T_{mb})$

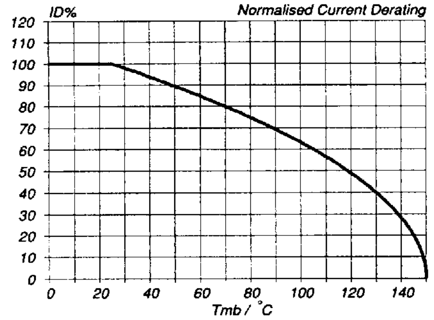


Fig.2. Normalised continuous drain current. ID% = $100 \cdot I_D/I_{D\,25\,^\circ C} = f(T_{mb})$; conditions: $V_{GS} \geq 10$ V

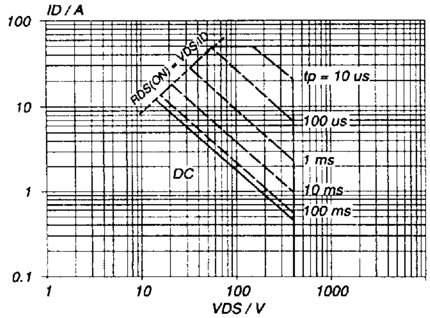


Fig.3. Safe operating area. $T_{mb} = 25$ °C
I_D & $I_{DM} = f(V_{DS})$; I_{DM} single pulse; parameter t_p

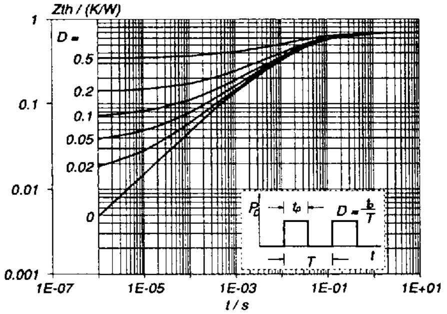


Fig.4. Transient thermal impedance. $Z_{th\,j\text{-}mb} = f(t)$; parameter $D = t_p/T$

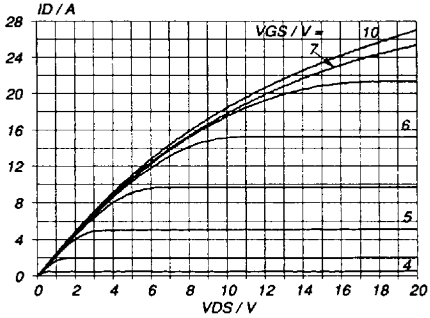


Fig.5. Typical output characteristics, $T_j = 25$ °C.
$I_D = f(V_{DS})$; parameter V_{GS}

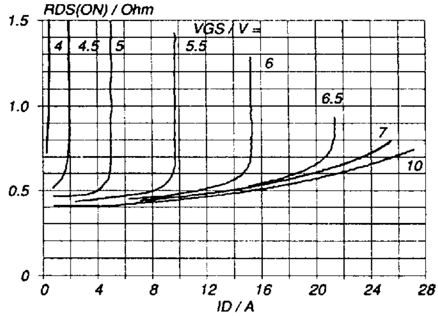


Fig.6. Typical on-state resistance, $T_j = 25$ °C.
$R_{DS(ON)} = f(I_D)$; parameter V_{GS}

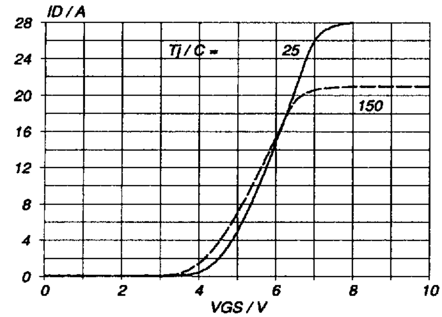


Fig.7. Typical transfer characteristics.
$I_D = f(V_{GS})$; conditions: $V_{DS} = 25$ V; parameter T_j

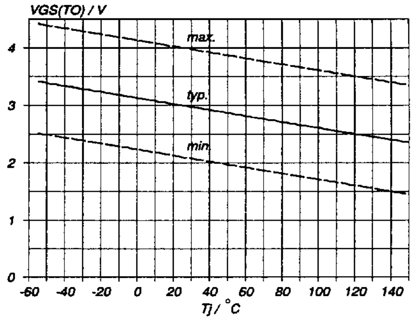


Fig.10. Gate threshold voltage.
$V_{GS(TO)} = f(T_j)$; conditions: $I_D = 1$ mA; $V_{DS} = V_{GS}$

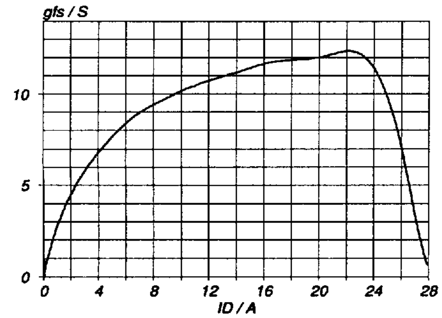


Fig.8. Typical transconductance, $T_j = 25$ °C.
$g_{fs} = f(I_D)$; conditions: $V_{DS} = 25$ V

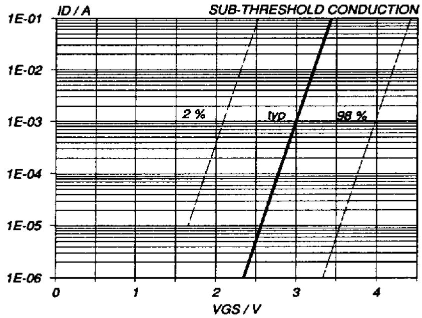


Fig.11. Sub-threshold drain current.
$I_D = f(V_{GS})$; conditions: $T_j = 25$ °C; $V_{DS} = V_{GS}$

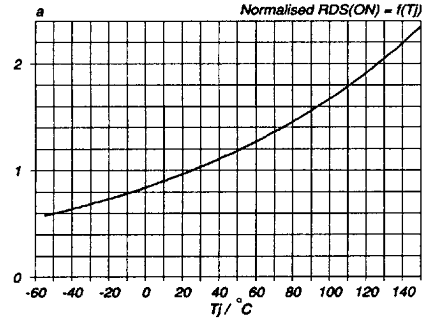


Fig.9. Normalised drain-source on-state resistance.
$a = R_{DS(ON)}/R_{DS(ON)25\,^{\circ}C} = f(T_j)$; $I_D = 6.5$ A; $V_{GS} = 10$ V

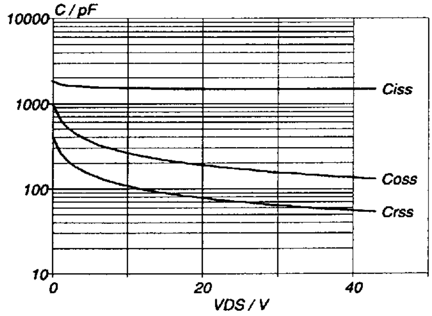


Fig.12. Typical capacitances, C_{iss}, C_{oss}, C_{rss}.
$C = f(V_{DS})$; conditions: $V_{GS} = 0$ V; $f = 1$ MHz

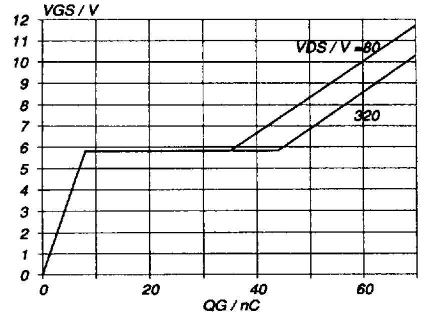


Fig.13. Typical turn-on gate-charge characteristics.
$V_{GS} = f(Q_G)$; *conditions:* $I_D = 14$ *A; parameter* V_{DS}

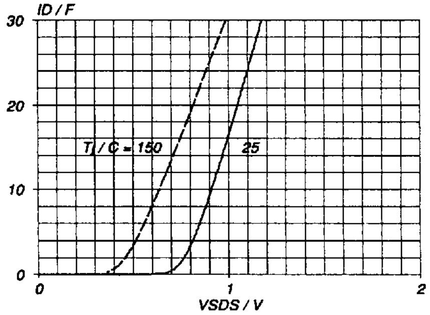


Fig.14. Typical reverse diode current.
$I_F = f(V_{SDS})$; *conditions:* $V_{GS} = 0$ *V; parameter* T_j